

KSC2233

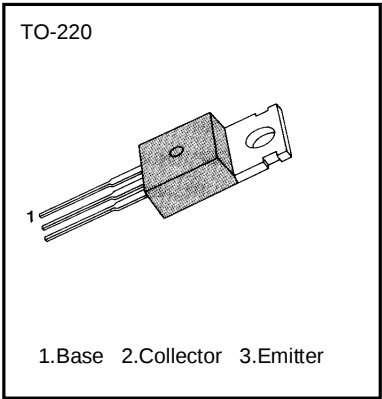
NPN EPITAXIAL SILICON TRANSISTOR

B/W TV HORIZONTAL DEFLECTION OUTPUT

- Collector-Base Voltage : $V_{CBO} = 200V$
- Collector Current (D.C) : $I_C = 4A$
- Collector Dissipation : $P_C = 40W$

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	4	A
Collector Dissipation ($T_C=25^{\circ}C$)	P_C	40	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 1mA, I_E = 0$	200			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 20mA, I_B = 0$	60			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 1mA, I_C = 0$	5			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 170V, I_E = 0$			10	μA
DC Current Gain	h_{FE1}	$V_{CE} = 5V, I_C = 1A$	30		150	
	h_{FE2}	$V_{CE} = 5V, I_C = 4A$	20	40		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 0.4A$			1	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 4A, I_B = 0.4A$			1.5	V
Current Gain-Band Width Product	f_T	$V_{CE} = 5V, I_C = 0.5A$		10		MHz



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